Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ Max	I_D T_A = +25°C
-60V	105mΩ @ V_{GS} = -10V	-3.3A
	130mΩ @ V_{GS} = -4.5V	-3.0A

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

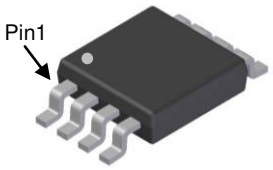
Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.074 grams (Approximate)

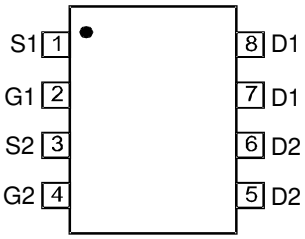
Applications

- DC-DC Converters
- Power Management Functions
- Backlighting

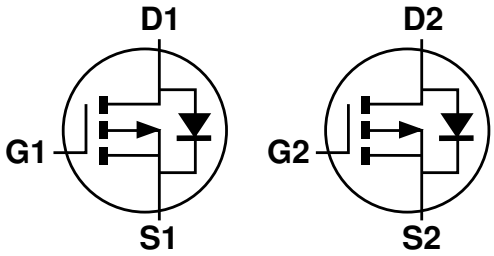
SO-8



Top View



Top View
Pin Configuration



Equivalent Circuit

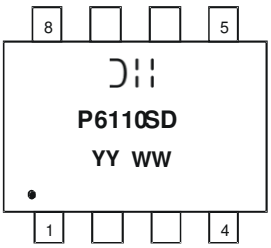
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP6110SSD-13	SO-8	2,500/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

SO-8



= Manufacturer's Marking
P6110SD = Product Type Marking Code
YYWW = Date Code Marking
YY or $\overline{YY}$ = Year (ex: 16 = 2016)
WW = Week (01 - 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	-60	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = -10V	T_C = +25°C T_C = +70°C	I_D	-7.8 -6.3	A
	T_A = +25°C T_A = +70°C	I_D	-3.3 -2.7	A
Pulsed Drain Current (380µs Pulse, 1% Duty Cycle)		I_{DM}	-24	A
Maximum Continuous Body Diode Forward Current (Note 6)		I_S	-1.8	A
Avalanche Current (Note 9) L = 0.1mH		I_{AS}	-19	A
Avalanche Energy (Note 9) L = 0.1mH		E_{AS}	18	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5 & 7)	T_A = +25°C	P_D	1.2	W
	T_A = +70°C		0.9	
Total Power Dissipation (Note 5 & 8)	T_A = +25°C		1.2	
Thermal Resistance, Junction to Ambient (Note 5 & 7)	Steady State	$R_{\Theta JA}$	104	°C/W
	t<10s		45	
Thermal Resistance, Junction to Ambient (Note 5 & 8)	Steady State		100	
Total Power Dissipation (Note 6 & 7)	T_A = +25°C	P_D	1.7	W
	T_A = +70°C		1.1	
Total Power Dissipation (Note 6 & 8)	T_A = +25°C		1.8	
Thermal Resistance, Junction to Ambient (Note 6 & 7)	Steady State	$R_{\Theta JA}$	74	°C/W
	t<10s		37	
Thermal Resistance, Junction to Ambient (Note 6 & 8)	Steady State		71	
Thermal Resistance, Junction to Case (Note 6 & 7)		$R_{\Theta JC}$	15	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. For a dual device with one active die.
8. For a device with two active die running at equal power.
9. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 10)						
Drain-Source Breakdown Voltage	BV_{DSS}	-60	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	-1	µA	V_{DS} = -48V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	100	nA	V_{GS} = ±16V, V_{DS} = 0V
ON CHARACTERISTICS (Note 10)						
Gate Threshold Voltage	$V_{GS(TH)}$	-1	—	-3	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	—	105	mΩ	V_{GS} = -10V, I_D = -4.5A
		—	—	130		V_{GS} = -4.5V, I_D =-3.5A
Diode Forward Voltage	V_{SD}	—	-0.7	-1.2	V	V_{GS} = 0V, I_S = -1A
DYNAMIC CHARACTERISTICS (Note 11)						
Input Capacitance	C_{ISS}	—	969	—	pF	VDS = -30V, VGS = 0V, f = 1.0MHz
Output Capacitance	C_{OSS}	—	57	—	pF	
Reverse Transfer Capacitance	C_{RSS}	—	44	—	pF	
Gate Resistance	R_G	—	13.7	—	Ω	VDS = 0V, VGS = 0V, f = 1.0MHz
Total Gate Charge (V_{GS} = -4.5V)	Q_G	—	8.2	—	nC	VDS = -30V, ID = -12A
Total Gate Charge (V_{GS} = -10V)	Q_G	—	17.2	—	nC	VDS = -30V, ID = -12A
Gate-Source Charge	Q_{GS}	—	3.0	—	nC	
Gate-Drain Charge	Q_{GD}	—	3.1	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	4.4	—	ns	V_{GS} = -10V, V_{DS} = -30V, R_{GEN} = 3Ω, ID=-12A
Turn-On Rise Time	t_R	—	23	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	34	—	ns	
Turn-Off Fall Time	t_F	—	42	—	ns	
Body Diode Reverse Recovery Time	t_{RR}	—	13.2	—	ns	I_S = -12A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q_{RR}	—	6.18	—	nC	

Notes: 10. Short duration pulse test used to minimize self-heating effect.
11. Guaranteed by design. Not subject to product testing.

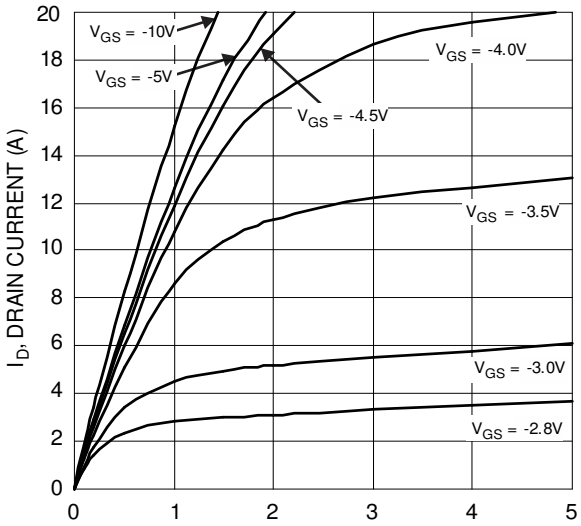


Figure 1 Typical Output Characteristics

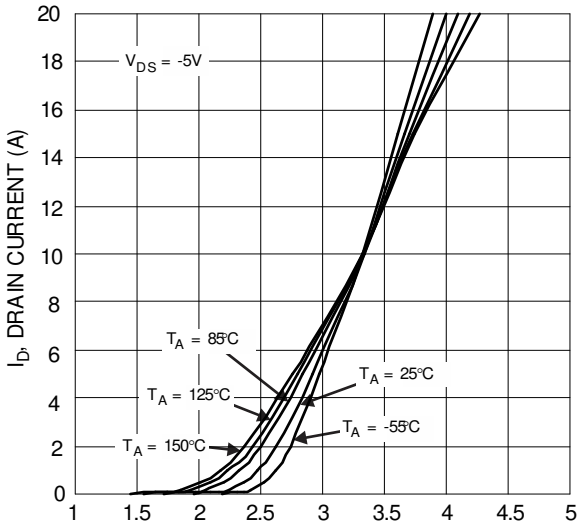


Figure 2 Typical Transfer Characteristics

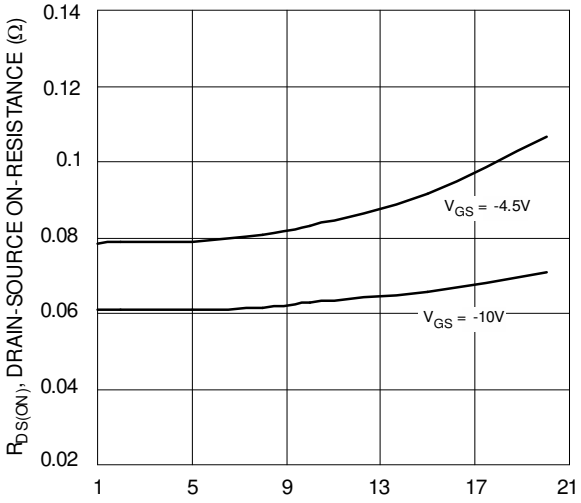


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

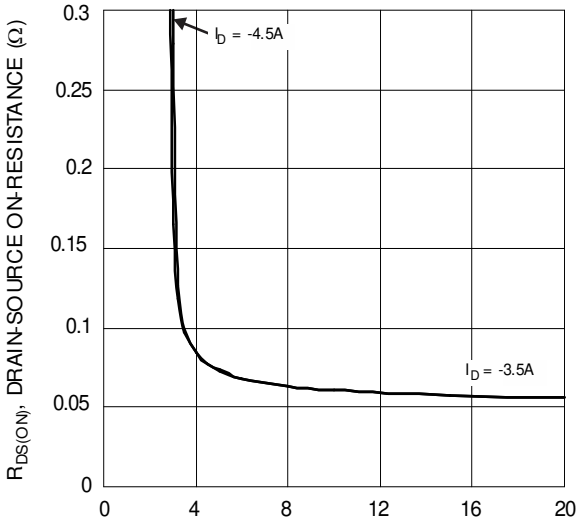


Figure 4 Typical Transfer Characteristics

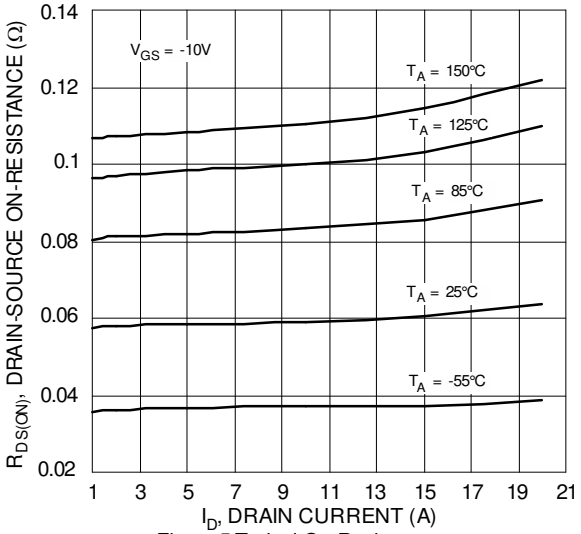


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

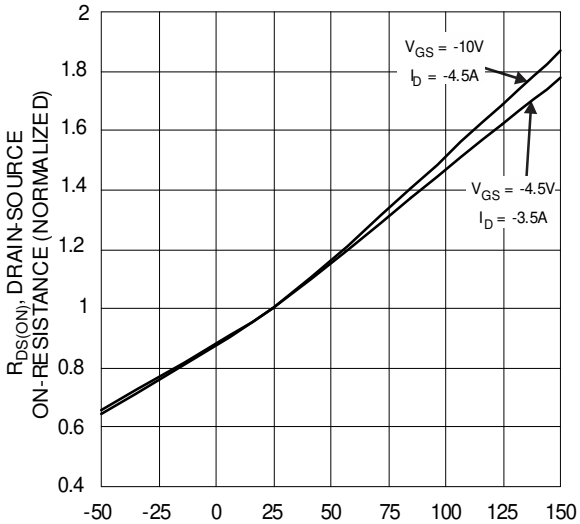


Figure 6 On-Resistance Variation with Temperature

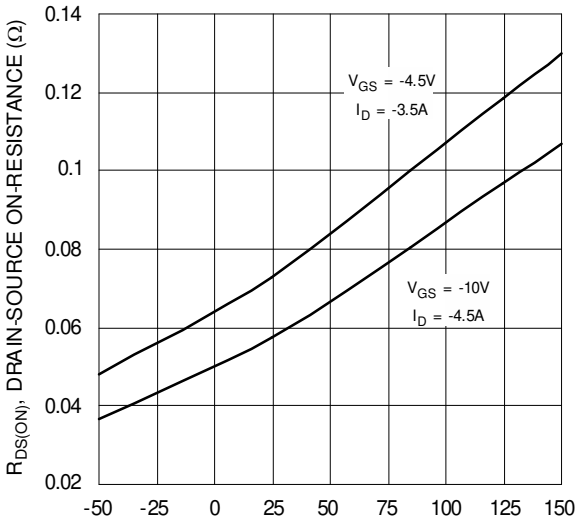


Figure 7 On-Resistance Variation with Temperature

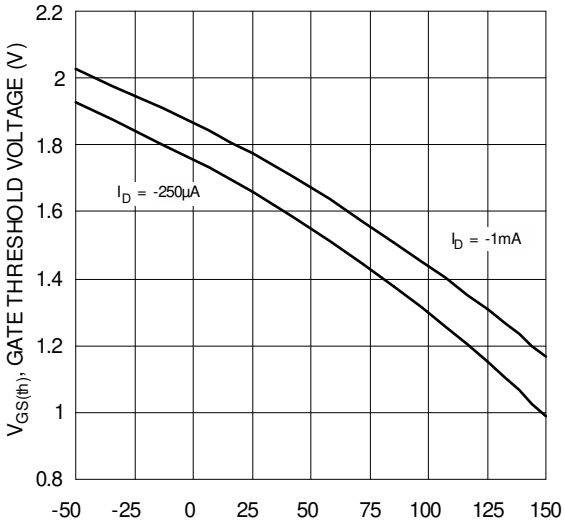


Figure 8 Gate Threshold Variation vs. Junction Temperature

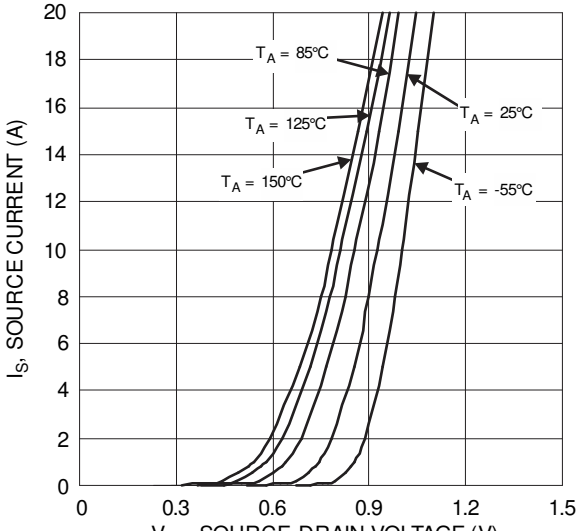


Figure 9 Diode Forward Voltage vs. Current

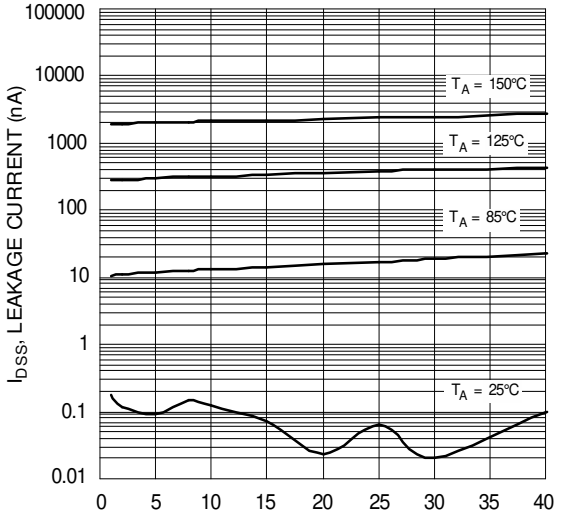


Figure 10 Typical Drain-Source Leakage Current vs. Voltage

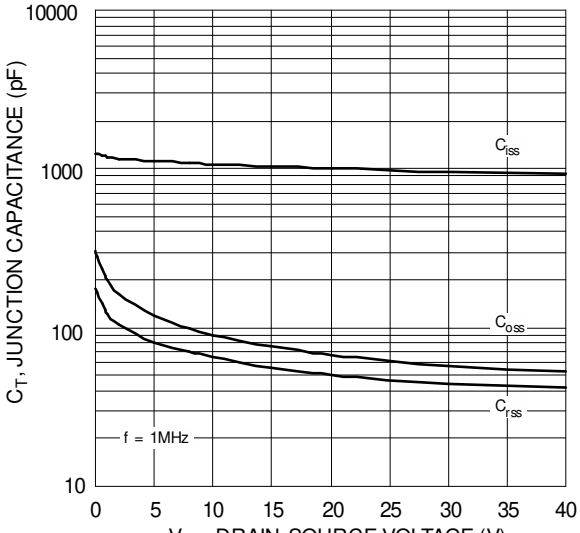


Figure 11 Typical Junction Capacitance

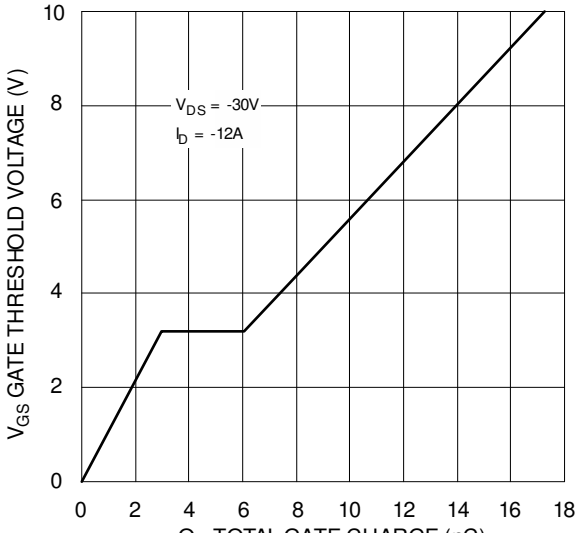


Figure 12 Gate Charge

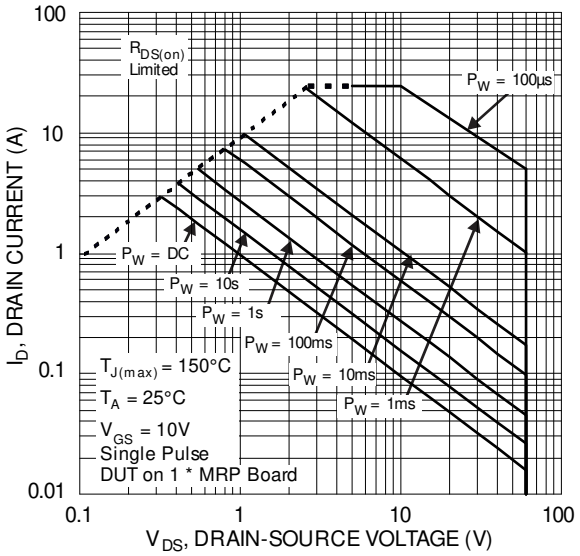


Figure 13 SOA, Safe Operation Area

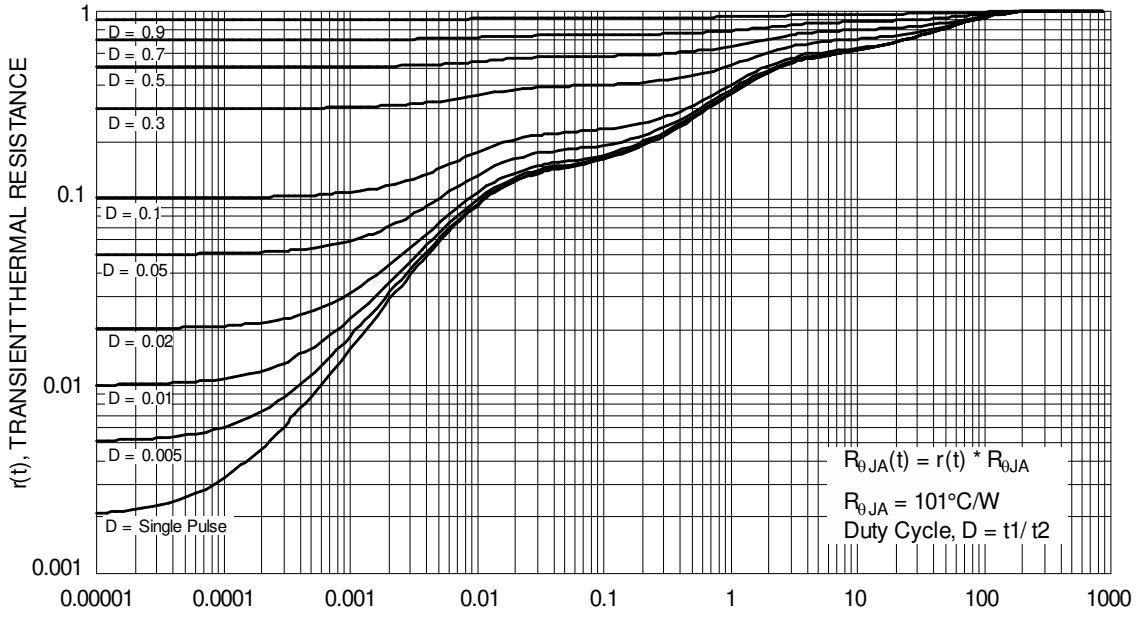
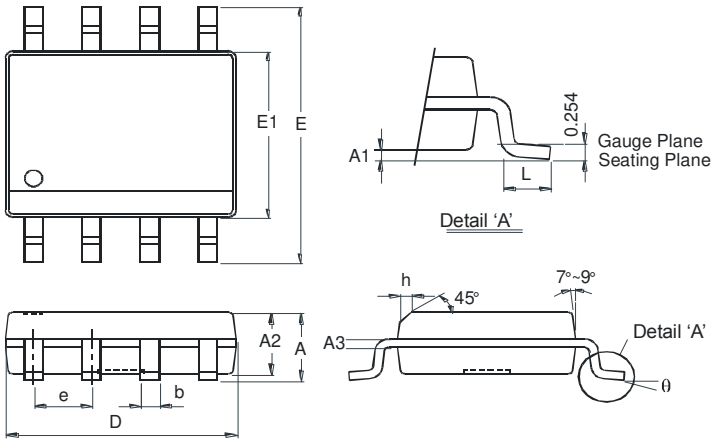


Figure 14 Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8

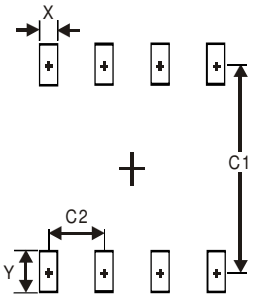


SO-8		
Dim	**Min**	**Max**
A	–	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	–	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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